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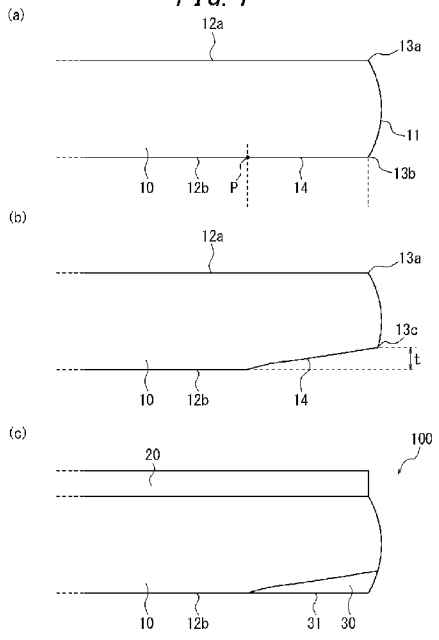
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(54) Title: METHOD OF PRODUCING EPITAXIAL WAFER AND THE EPITAXIAL WAFER

[Fig. 1]

FIG. 1



(57) Abstract: The present invention provides a method of producing an epitaxial wafer having a highly flat rear surface without polishing top and rear surfaces of the epitaxial wafer after forming an epitaxial film. A method of producing an epitaxial wafer 100 according to the present invention comprises a step of preparing a semiconductor wafer 10 having a beveled portion 11 formed on its end portion, a first surface 12b, a second surface 12a opposite to the first surface 12b, and edges 13b and 13a on both of the first surface12b and the second surface12a, the each edge 13a and 13b is boundary with the beveled portion 11; a step of processing of rolling off an outer peripheral portion 14 of the first surface 12b to form a roll-off region, the outer peripheral portion 14 is extending outward of the wafer from a predetermined position P inner than the position of the edge 13b on the first surface 12b; and a step of forming a first epitaxial film 20 on the second surface 12a.

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